## CERTIFICATE OF MAILING PURSUANT TO 37 C.F.R. §1.8

I hereby certify that this correspondence, pursuant to 37 C.F.R. §1.8, is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, MAIL STOP AMENDMENT, PO Box 1450, Alexandria, VA 22313-1450, on:

1-24-2004

BY: Julie A. Eslecte

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT PURSUANT TO 37 C.F.R. §§1.97-1.98

PATENT APPLICATION

Applicant(s):

Kaoru INOUE, et al.

Docket No.:

28569.7636

Serial No.:

10/711,134

Filing Date:

August 26, 2004

Group Art Unit:

TBD

Confirmation No.:

5133

TITLE:

SEMICONDUCTOR DEVICE

Examiner:

TBD

Commissioner for Patents MAIL STOP AMENDMENT PO Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure under 37 C.F.R. §1.56 and pursuant to 37 C.F.R. §§1.97-1.98, the reference or references listed and identified on the attached PTO-1449 based form are being submitted here for consideration by the Examiner. Any copy of the items listed on the enclosed copy of Form PTO-1449 that is not enclosed with this Information Disclosure Statement was previously cited by or submitted to the Patent and Trademark Office in the prior Parent Application, U.S. Serial No. 09/733,593, under 37 C.F.R. §1.98, which application was filed on December 8, 2000 and issued as U.S. Patent No. 6,639,255 on October 28, 2003.

The reference or references are being cited only in the interest of candor and without any admission that they constitute statutory prior art or contain matter which anticipates the invention or which would render the same obvious, either singly or in combination, to a person of ordinary skill in the art.



Serial No.: 10/711,134

Title: SEMICONDUCTOR DEVICE

This Information Disclosure Statement (IDS) is being filed under 37 C.F.R. §1.97(b)(1) as each item of information contained in this disclosure is being submitted within three months of the filing of this application, as such no fee should be required. If Applicant has overlooked any fees, however, the Commissioner is hereby authorized to debit Deposit Account No. 19-2814 for the same. A duplicate copy of this Information Disclosure Statement is enclosed for this purpose.

If there are any questions concerning this IDS, the Examiner is requested to contact the undersigned. If it is determined that this IDS has been filed under the wrong rule, the United States Patent and Trademark Office is requested to consider this IDS under the proper rule (with a petition if necessary) and charge the appropriate fee to Deposit Account No. 19-2814.

Respectfully submitted,

Date: 9-23-04

Michael K. Kelly Reg. No. 32,848

45875

**Enclosures:** 

PTO-1449

Patent copies

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